

# MOSFET – N-Channel, UniFET™

500 V, 20 A, 230 mΩ

## FDP20N50/FDPF20N50 /FDPF20N50T

### Description

UniFET MOSFET is onsemi's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

### Features

- $R_{DS(on)} = 200 \text{ m}\Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 10 \text{ A}$
- Low Gate Charge (Typ. 45.6 nC)
- Low  $C_{rss}$  (Typ. 27 pF)
- 100% Avalanche Tested

### Applications

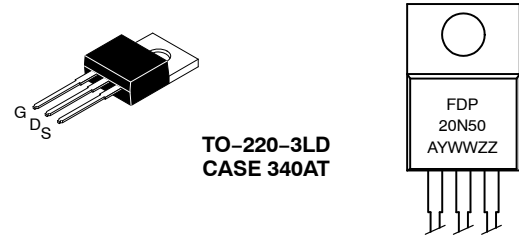
- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply

$V_{DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
500 V	230 mΩ @ 10 V	20 A

### MARKING DIAGRAMS

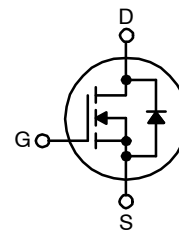


FDPF20N50(T) = Specific Device Code  
A = Assembly Location  
YWW = Date Code (Year & Week)  
ZZ = Assembly Lot



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### N-CHANNEL MOSFET



### ORDERING INFORMATION

See detailed ordering and shipping information on page 9 of this data sheet.

## FDP20N50/FDPF20N50

### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter		FDP20N50	FDPF20N50/ FDPF20N50T	Unit
V <sub>DSS</sub>	Drain-Source Voltage		500		V
I <sub>D</sub>	Drain Current	Continuous (T <sub>C</sub> = 25°C)	20	20*	A
		Continuous (T <sub>C</sub> = 100°C)	12.9	12.9*	
I <sub>DM</sub>	Drain Current	Pulsed (Note 1)	80	80*	A
V <sub>GSS</sub>	Gate-Source Voltage		±30		V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		1110		mJ
I <sub>AR</sub>	Avalanche Current (Note 1)		20		A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		25		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C)	250	38.5	W
		Derate above 25°C	2.0	0.3	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150		°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

\*Drain current limited by maximum junction temperature.

1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. L = 5.0 mH, I<sub>AS</sub> = 20 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.

3. I<sub>SD</sub> ≤ 20 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C.

### THERMAL CHARACTERISTICS

Symbol	Parameter	FDP20N50	FDPF20N50/ FDPF20N50T	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case, Max.	0.5	3.3	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	

# FDP20N50/FDPF20N50

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	500	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	–	0.5	–	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 400 V, T <sub>C</sub> = 125°C	–	–	1 10	μA μA
I <sub>GSSF</sub>	Gate–Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V	–	–	100	nA
I <sub>GSSR</sub>	Gate–Body Leakage Current, Reverse	V <sub>GS</sub> = –30 V, V <sub>DS</sub> = 0V	–	–	–100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3.0	–	5.0	V
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	–	0.20	0.23	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 10 A	–	24.6	–	S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	–	2400	3120	pF
C <sub>oss</sub>	Output Capacitance		–	355	465	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		–	27	–	pF

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn–On Delay Time	V <sub>DD</sub> = 250 V, I <sub>D</sub> = 20 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 25 Ω (Note 4)	–	95	200	ns
t <sub>r</sub>	Turn–On Rise Time		–	375	760	ns
t <sub>d(off)</sub>	Turn–Off Delay Time		–	100	210	ns
t <sub>f</sub>	Turn–Off Fall Time		–	105	220	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 20 A, V <sub>GS</sub> = 10 V (Note 4)	–	45.6	59.5	nC
Q <sub>gs</sub>	Gate–Source Charge		–	14.8	–	nC
Q <sub>gd</sub>	Gate–Drain Charge		–	21.6	–	nC

### DRAIN–SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I <sub>S</sub>	Maximum Continuous Drain–Source Diode Forward Current		–	–	30	A
I <sub>SM</sub>	Maximum Pulsed Drain–Source Diode Forward Current		–	–	80	A
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 20 A	–	–	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 20 A, dI <sub>F</sub> /dt = 100 A/μs	–	507	–	ns
Q <sub>rr</sub>	Reverse Recovery Charge		–	7.20	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

# FDP20N50/FDPF20N50

## TYPICAL CHARACTERISTICS

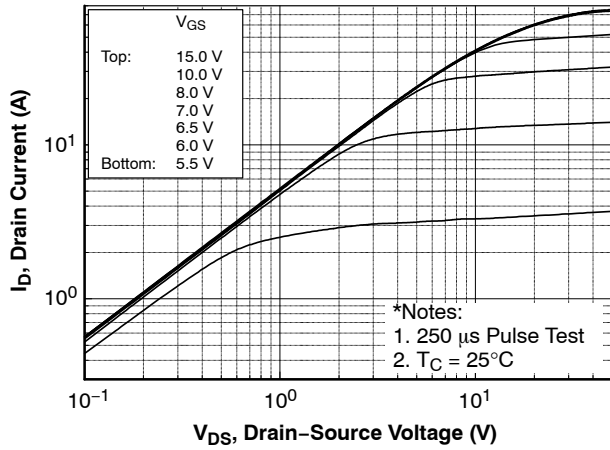


Figure 1. On-Region Characteristics

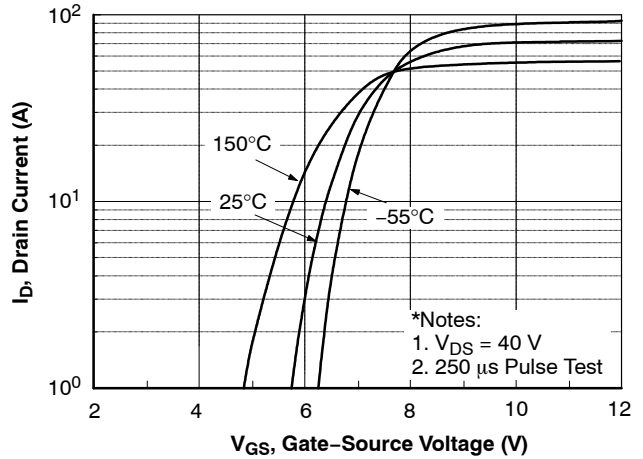


Figure 2. Transfer Characteristics

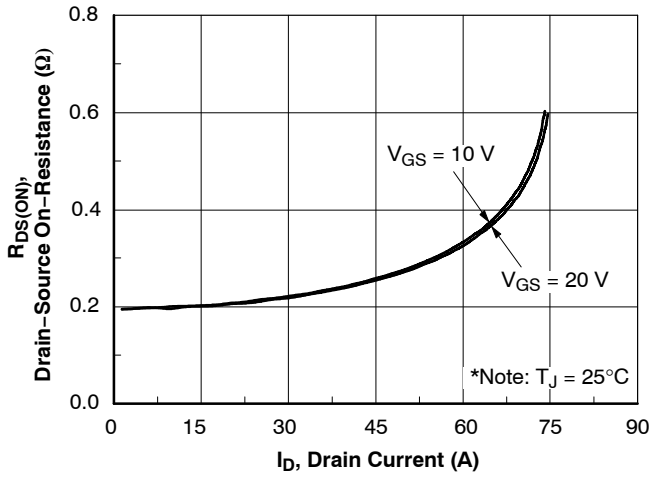


Figure 3. On-Resistance Variation vs. Drain Current and Gate voltage

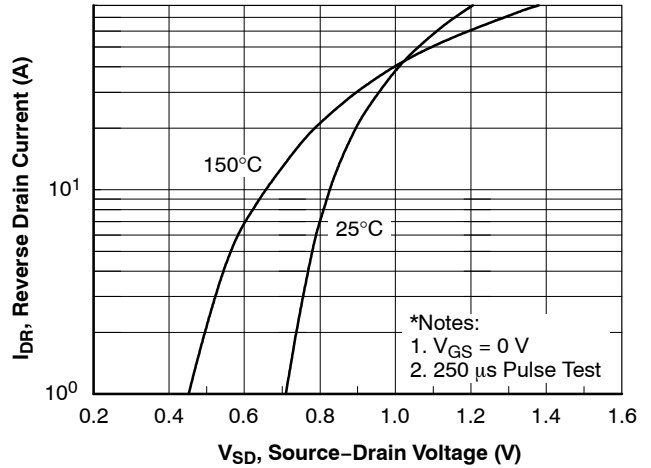


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

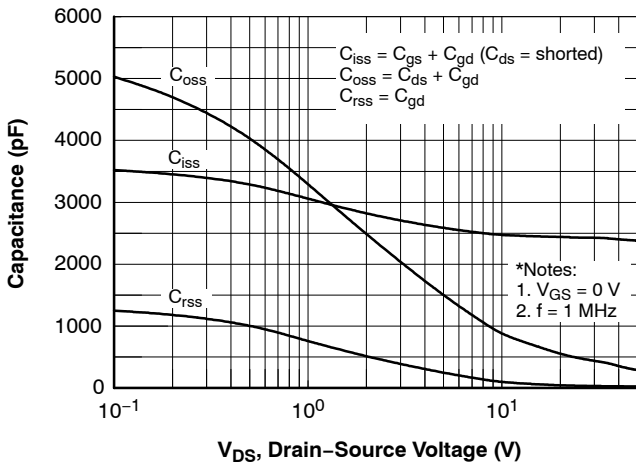


Figure 5. Capacitance Characteristics

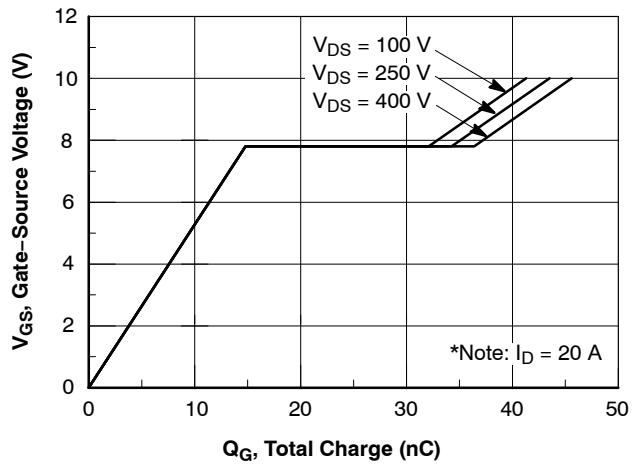
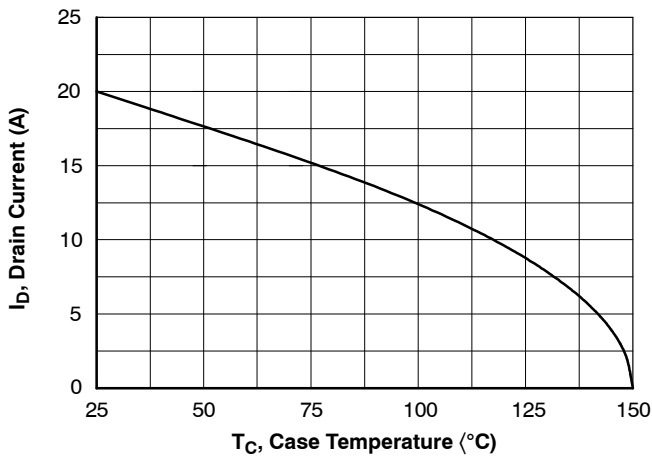
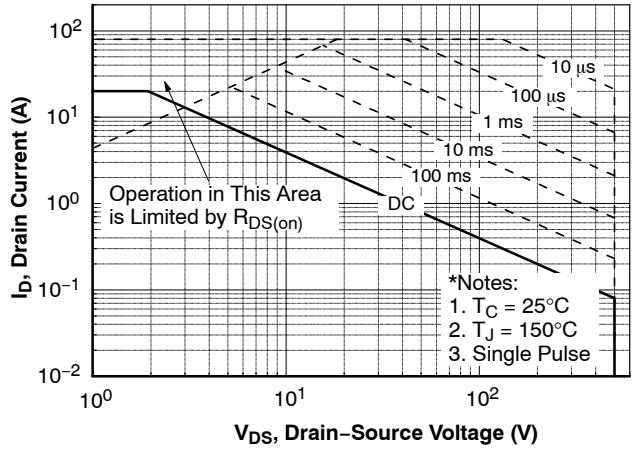
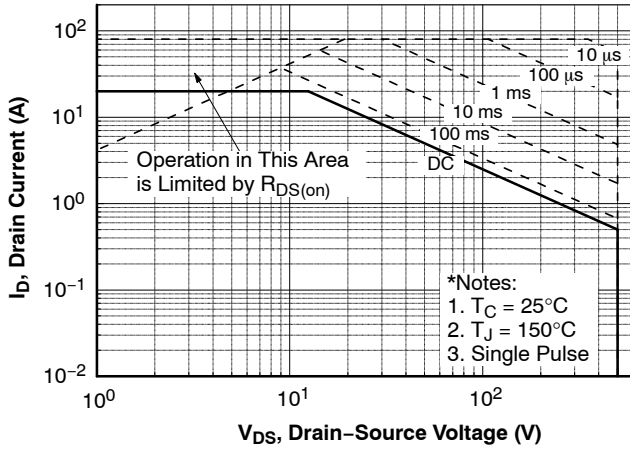
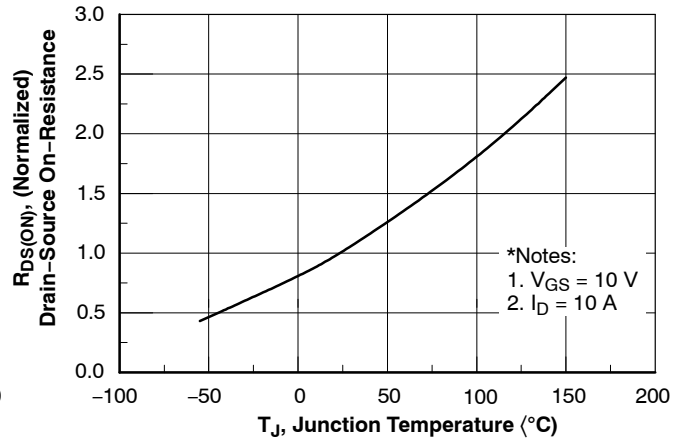
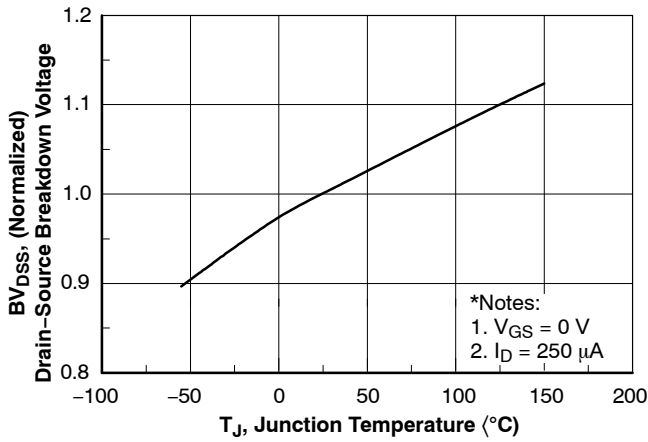


Figure 6. Gate Charge Characteristics

# FDP20N50/FDPF20N50

## TYPICAL CHARACTERISTICS (CONTINUED)



# FDP20N50/FDPF20N50

## TYPICAL CHARACTERISTICS (CONTINUED)

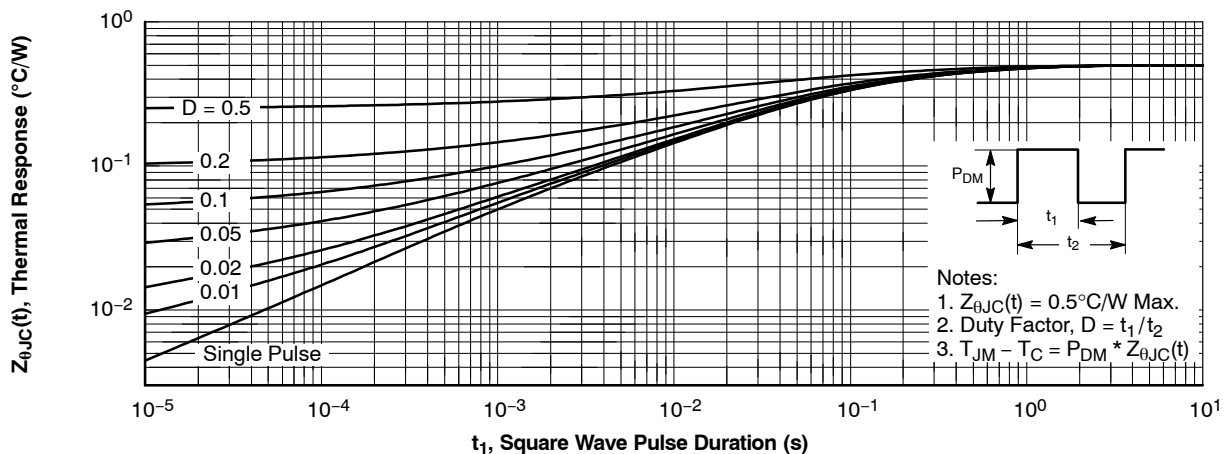


Figure 13. Transient Thermal Response Curve – FDP20N50

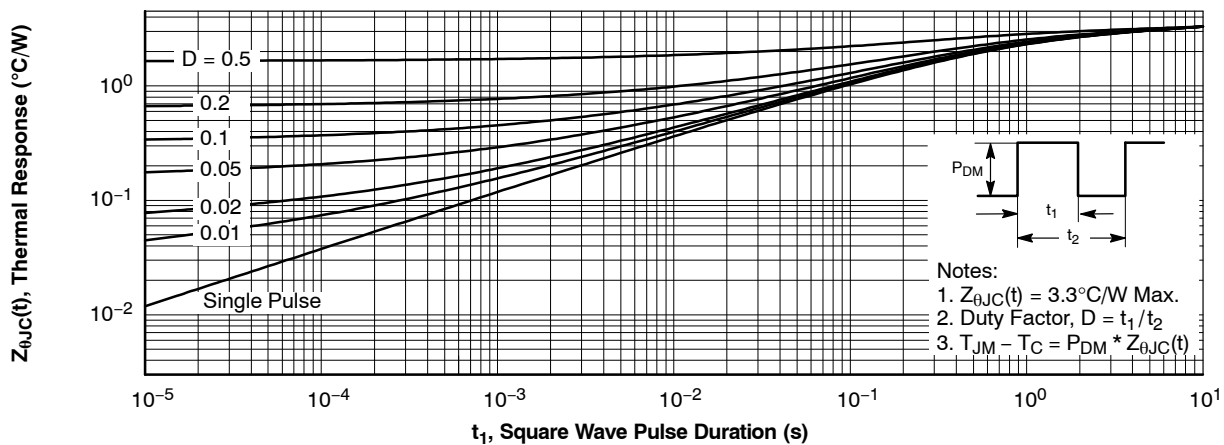
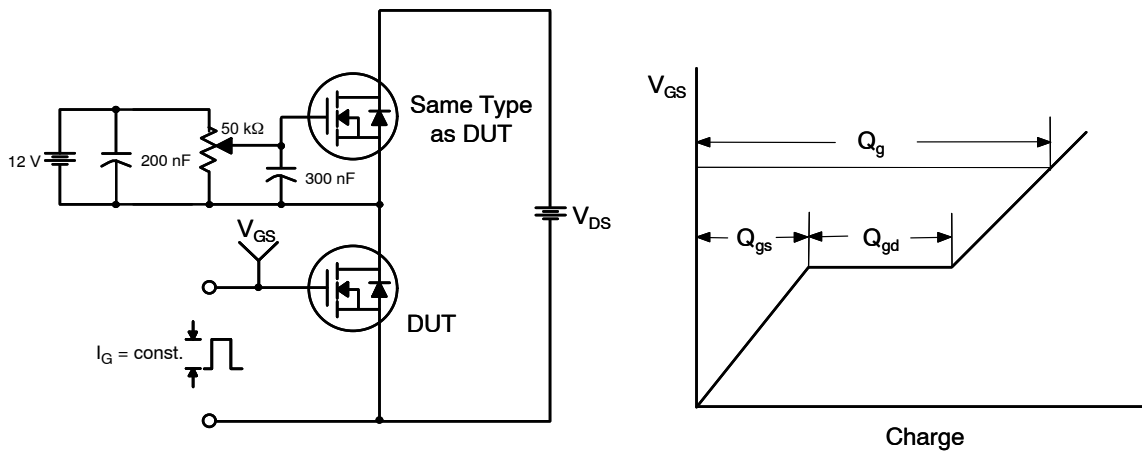
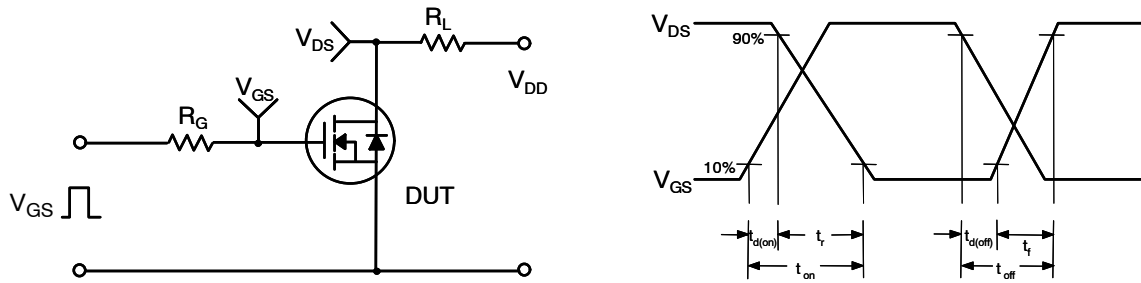


Figure 12. Transient Thermal Response Curve – FDPF20N50

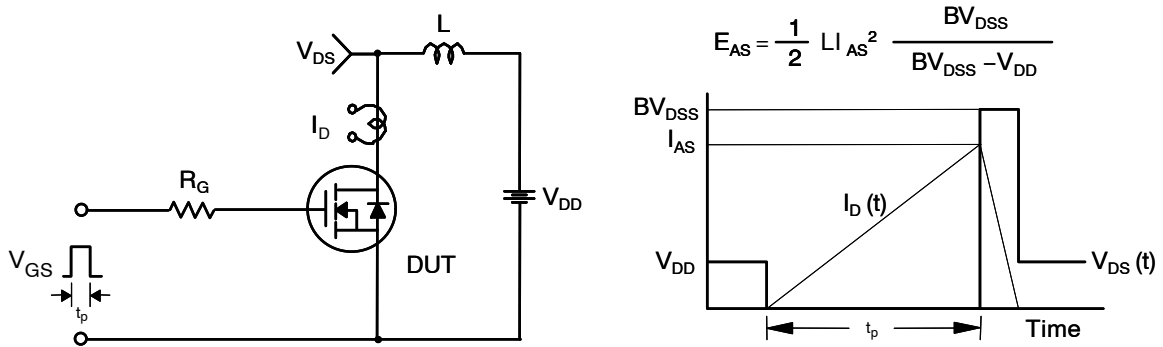
## FDP20N50/FDPF20N50



**Figure 14. Gate Charge Test Circuit & Waveform**



**Figure 15. Resistive Switching Test Circuit & Waveforms**



**Figure 16. Unclamped Inductive Switching Test Circuit & Waveforms**

# FDP20N50/FDPF20N50

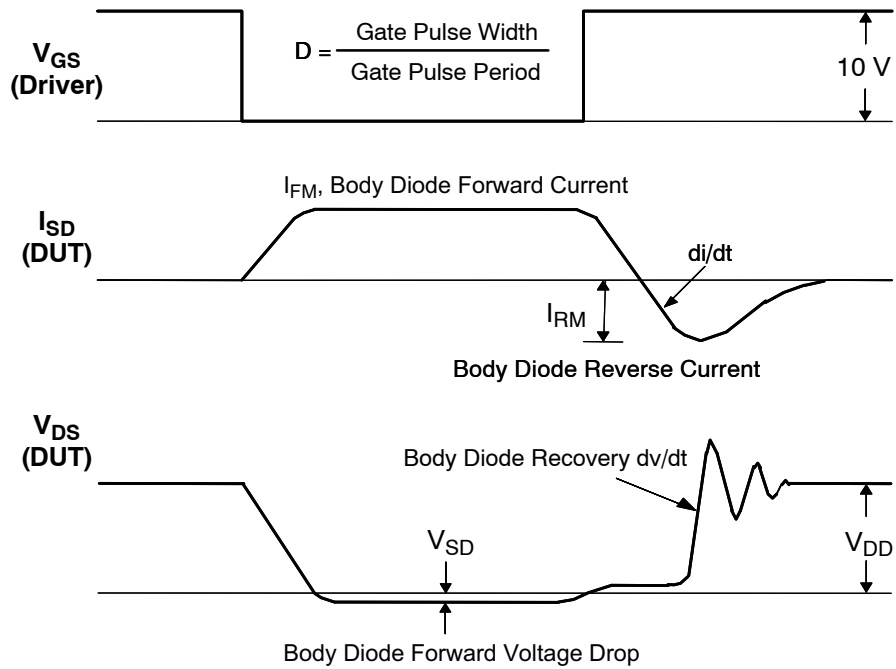
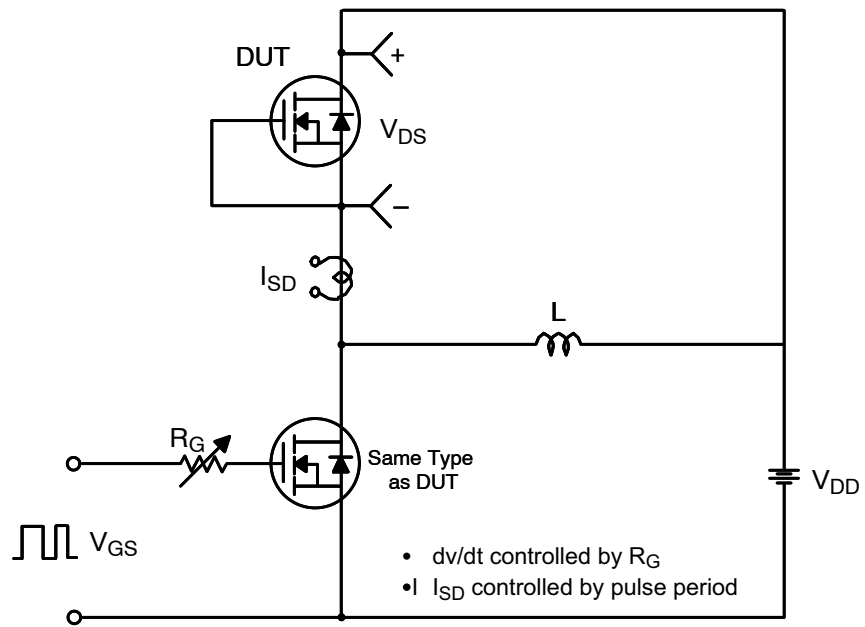


Figure 17. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms



## FDP20N50/FDPF20N50

### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Quantity
FDP20N50	FDP20N50	TO-220-3LD CASE 340AT	1000 Units / Tube
FDPF20N50	FDPF20N50	TO-220 Fullpack, 3-Lead / TO-220F-3SG CASE 221AT	1000 Units / Tube
FDPF20N50T	FDPF20N50	TO-220 Fullpack, 3-Lead / TO-220F-3SG CASE 221AT	1000 Units / Tube

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# MECHANICAL CASE OUTLINE

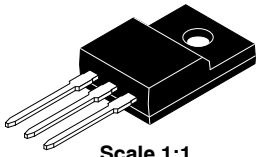
## PACKAGE DIMENSIONS

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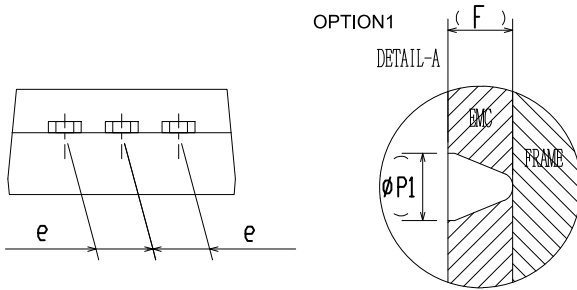
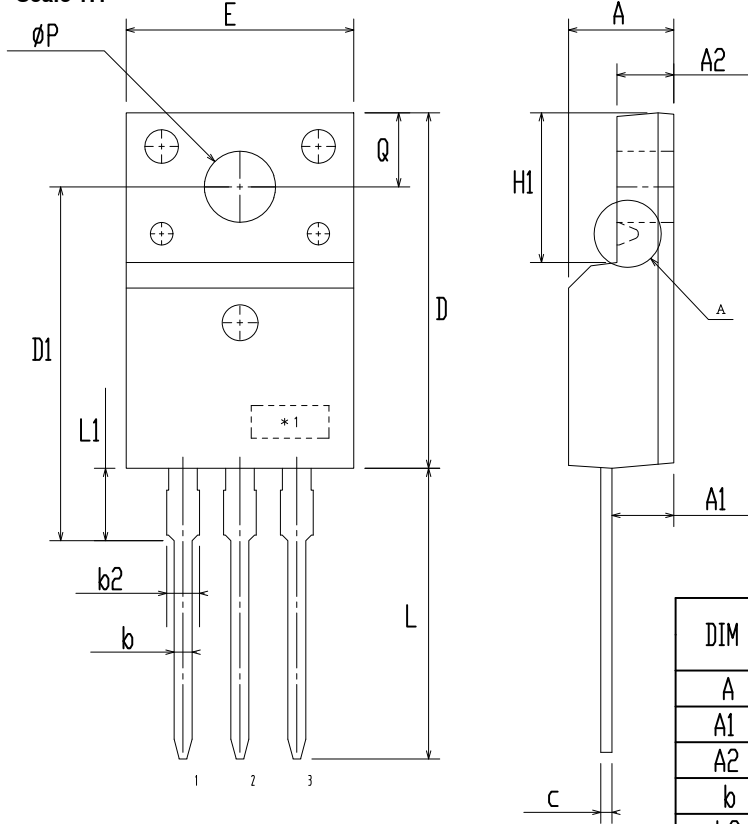


### TO-220 Fullpack, 3-Lead / TO-220F-3SG CASE 221AT ISSUE B

DATE 19 JAN 2021



Scale 1:1



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.50	4.70	4.90
A1	2.56	2.76	2.96
A2	2.34	2.54	2.74
b	0.70	0.80	0.90
b2	~	~	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.60	15.80	16.00
E	9.96	10.16	10.36
e	2.34	2.54	2.74
F	~	0.84	~
H1	6.48	6.68	6.88
L	12.78	12.98	13.18
L1	3.03	3.23	3.43
phi P	2.98	3.18	3.38
phi P1	~	1.00	~
Q	3.20	3.30	3.40

**NOTES:**

- A. DIMENSION AND TOLERANCE AS ASME Y14.5-2009
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUCTIONS.
- C. OPTION 1 - WITH SUPPORT PIN HOLE  
OPTION 2 - NO SUPPORT PIN HOLE

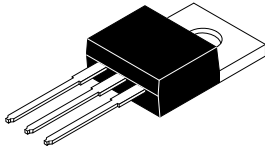
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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

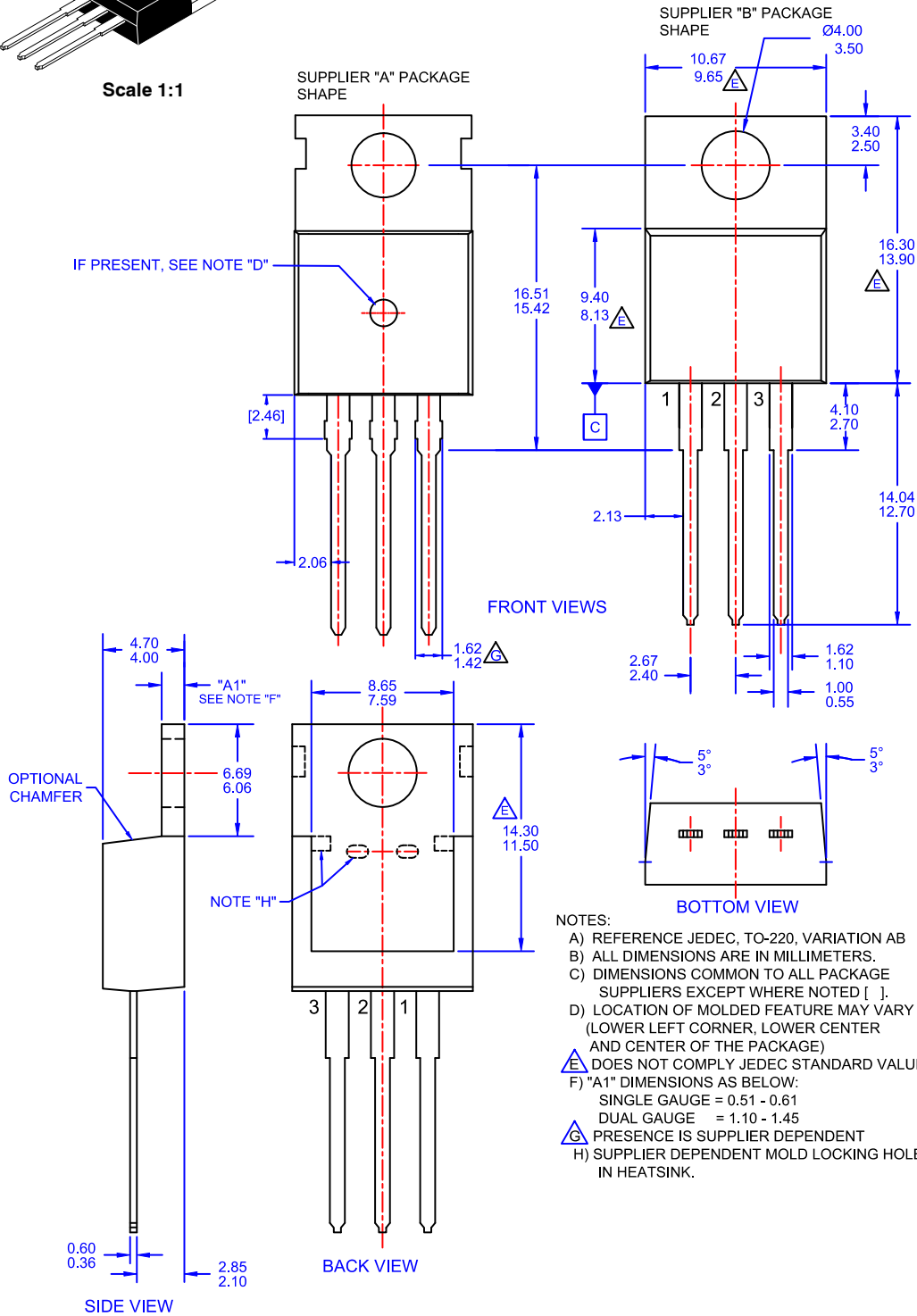
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Scale 1:1

### TO-220-3LD CASE 340AT ISSUE A

DATE 03 OCT 2017



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